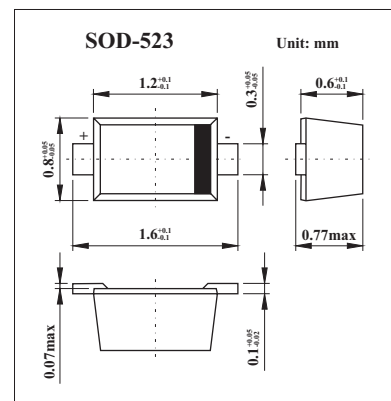


## Band-switching diode

## BA891

## ■ Features

- Very small plastic SMD package
- Low diode capacitance: max. 1.05 pF
- Low diode forward resistance: max. 0.7  $\Omega$
- Small inductance.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	$V_R$			35	V
Continuous forward current	$I_F$			100	mA
Total power dissipation	$P_{tot}$	$T_s = 90^\circ\text{C}$		715	mW
Storage temperature	$T_{stg}$		-65	+150	$^\circ\text{C}$
Junction temperature	$T_j$		-65	+150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Typ	Max	Unit
Forward voltage	$V_F$	$I_F = 10\text{ mA}$		1	V
Reverse current	$I_R$	$V_R = 30\text{ V}$		20	nA
Diode capacitance	$C_d$	$f = 1\text{ MHz}$ ; note 1			
		$V_R = 1\text{ V}$	0.8	1.05	pF
		$V_R = 3\text{ V}$	0.65	0.9	pF
Diode forward resistance	$r_D$	$f = 100\text{ MHz}$ ; note 1			
		$I_F = 3\text{ mA}$	0.45	0.7	$\Omega$
		$I_F = 10\text{ mA}$	0.36	0.5	$\Omega$
Series inductance	$L_s$		0.6		nH

Note

1. Guaranteed on AQL basis; inspection level S4, AQL 1.0.

## ■ Marking

Marking	7
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